

RELIABILITY REPORT
FOR
MAX3013ExP
PLASTIC ENCAPSULATED/CHIP SCALE DEVICES

July 17, 2006

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.
SUNNYVALE, CA 94086

Written by

Jim Pedicord
Quality Assurance
Manager, Reliability Operations

Conclusion

The MAX3013 has completed qualification testing except for product level Burn-In. Package and Process qualification has been completed for the device.

Table of Contents

I.Device Description	V.Quality Assurance Information
II.Manufacturing Information	VI.Reliability Evaluation
III.Packaging Information	IV.Die Information
.....Attachments	

I. Device Description

A. General

The MAX3013 8-channel level translator provides the level shifting necessary to allow 100Mbps data transfer in a multivoltage system. Externally applied voltages, V_{CC} and V_L , set the logic levels on either side of the device. Logic signals present on the V_L side of the device appear as a higher voltage logic signal on the V_{CC} side of the device, and vice-versa.

The MAX3013 features an EN input that, when at logic low, places all inputs/outputs on both sides in tristate and reduces the V_{CC} and V_L supply currents to 0.1 μ A. This device operates at a guaranteed data rate of 100Mbps for $V_L > 1.8V$.

The MAX3013 accepts a V_{CC} voltage from +1.65V to +3.6V and a V_L voltage from +1.2V to ($V_{CC} - 0.4V$), making it ideal for data transfer between low-voltage ASICs/PLDs and higher voltage systems. The MAX3013 is available in 5 x 4 UCSP™, 20-pin 5mm x 5mm QFN, and 20-pin TSSOP packages.

B. Absolute Maximum Ratings

<u>Item</u>	<u>Rating</u>
(All voltages referenced to GND.)	
V_{CC}	-0.3V to +4V
V_L	-0.3V to +4V
I/O V_{CC}	-0.3V to ($V_{CC} + 0.3V$)
I/O V_L	-0.3V to ($V_L + 0.3V$)
EN	-0.3V to ($V_L + 0.3V$)
Short-Circuit Duration I/O V_L , I/O V_{CC} to GND	Continuous
Continuous Power Dissipation ($T_A = +70^\circ C$)	
20-Pin TSSOP (derate 11mW/ $^\circ C$ above +70 $^\circ C$)	879mW
5 x 4 UCSP (derate 10mW/ $^\circ C$ above +70 $^\circ C$)	800mW
20-Pin QFN (derate 20.0mW/ $^\circ C$ above +70 $^\circ C$)	1.60W
Operating Temperature Range	-40 $^\circ C$ to +85 $^\circ C$
Junction Temperature	+150 $^\circ C$
Storage Temperature Range	-65 $^\circ C$ to +150 $^\circ C$
Lead Temperature (soldering, 10s)	+300 $^\circ C$

II. Manufacturing Information

A. Description/Function:	+1.2V to +3.6V, 0.1µA, 100Mbps, 8-Channel Level Translators
B. Process:	S4
C. Number of Device Transistors:	1447
D. Fabrication Location:	California, USA
E. Assembly Location:	Korea, Malaysia, Philippines, USA
F. Date of Initial Production:	January, 2004

III. Packaging Information

A. Package Type:	20-Pin TSSOP	5 x 4 UCSP	20-pin QFN-EP
B. Lead Frame:	Copper	N/A	Copper
C. Lead Finish:	Solder Plate or 100% Matte Tin	N/A	Solder Plate
D. Die Attach:	Silver-Filled Epoxy	N/A	Silver-Filled Epoxy
E. Bondwire:	Gold (1 mil dia.)	N/A	Gold (1 mil dia.)
F. Mold Material:	Epoxy with silica filler	N/A	Epoxy with silica filler
G. Assembly Diagram:	#05-9000-1673	#05-9000-1672	#05-9000-1998
H. Flammability Rating:	Class UL94-V0	Class UL94-V0	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C:	Level 1	Level 1	Level 1

IV. Die Information

A. Dimensions:	81 x 102 mils
B. Passivation:	Si ₃ N ₄ /SiO ₂ (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Aluminum/Si (Si = 1%)
D. Backside Metallization:	None
E. Minimum Metal Width:	Metal1, Metal2 & Metal3 = 0.6 microns (as drawn)
F. Minimum Metal Spacing:	Metal1, Metal2 & Metal3 = 0.4 microns (as drawn)
G. Bondpad Dimensions:	5 mil. Sq.
H. Isolation Dielectric:	SiO ₂
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

- A. Quality Assurance Contacts: Jim Pedicord (Manager, Rel Operations)
Bryan Preeshl (Managing Director of QA)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are pending. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 48 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

Temperature Acceleration factor assuming an activation energy of 0.8eV

$$\lambda = 22.91 \times 10^{-9}$$

$$\lambda = 22.91 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

This low failure rate represents data collected from Maxim's reliability monitor program. In addition to routine production Burn-In, Maxim pulls a sample from every fabrication process three times per week and subjects it to an extended Burn-In prior to shipment to ensure its reliability. The reliability control level for each lot to be shipped as standard product is 59 F.I.T. at a 60% confidence level, which equates to 3 failures in an 80 piece sample. Maxim performs failure analysis on any lot that exceeds this reliability control level. Attached Burn-In Schematic (Spec. # 06-6083) shows the static Burn-In circuit. Maxim also performs quarterly 1000 hour life test monitors. This data is published in the Product Reliability Report (**RR-1N**). Current monitor data for the S4 Process results in a FIT Rate of 0.37 @ 25C and 6.28 @ 55C (0.8 eV, 60% UCL)

B. Moisture Resistance Tests

Maxim pulls pressure pot samples from every assembly process three times per week. Each lot sample must meet an LTPD = 20 or less before shipment as standard product. Additionally, the industry standard 85°C/85%RH testing is done per generic device/package family once a quarter.

C. E.S.D. and Latch-Up Testing

The RT64 die type has been found to have all pins able to withstand a transient pulse of < ±200V per Mil-Std-883 Method 3015 (reference attached ESD Test Circuit). Latch-Up testing has shown that this device withstands a current of ±250mA.

Table 1
Reliability Evaluation Test Results

MAX3013ExPxx

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	PACKAGE	SAMPLE SIZE	NUMBER OF FAILURES
Static Life Test (Note 1)					
	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality		48	0
Moisture Testing (Note 2)					
Pressure Pot	Ta = 121°C P = 15 psi. RH= 100% Time = 168hrs.	DC Parameters & functionality	TSSOP/QFN	77	0
			UCSP	77	0
85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality	TSSOP/QFN UCSP	77 N/A	0 N/A
Mechanical Stress (Note 2)					
Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality	TSSOP/QFN	77	0
			UCSP	77	0

Note 1: Life Test Data may represent plastic DIP qualification lots.

Note 2: Generic Package/Process data

Note 3: UCSP Temperature Cycle performed at -40°C/125°C, 1000 Cycles, ramp rate 11°C/minute, dwell=15 minutes, one cycle/hour.

Attachment #1

TABLE II. Pin combination to be tested. 1/ 2/

	Terminal A (Each pin individually connected to terminal A with the other floating)	Terminal B (The common combination of all like-named pins connected to terminal B)
1.	All pins except V_{PS1} 3/	All V_{PS1} pins
2.	All input and output pins	All other input-output pins

1/ Table II is restated in narrative form in 3.4 below.

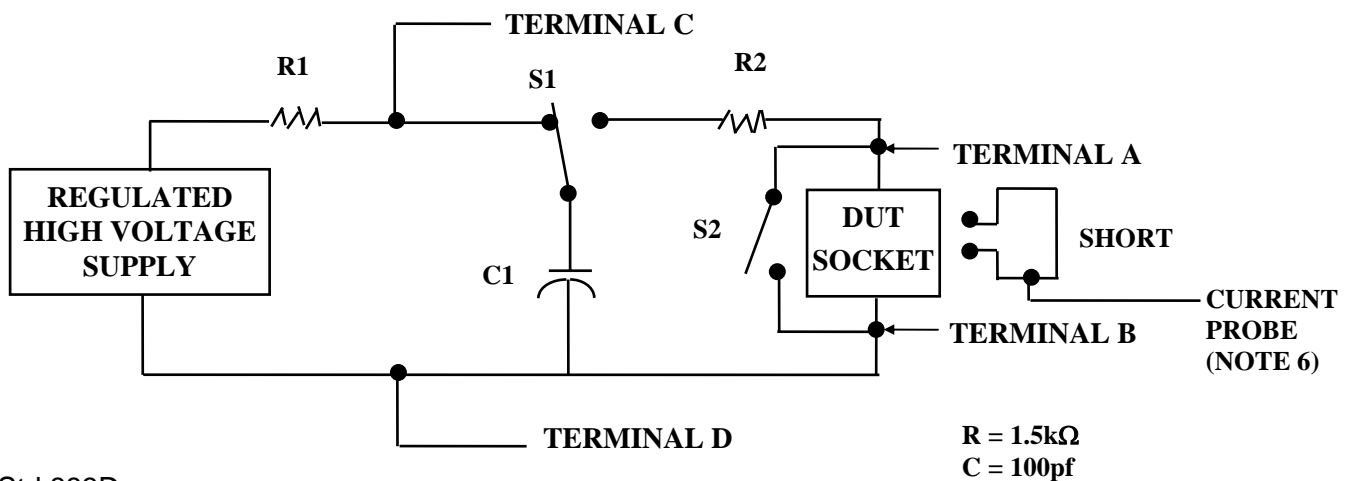
2/ No connects are not to be tested.

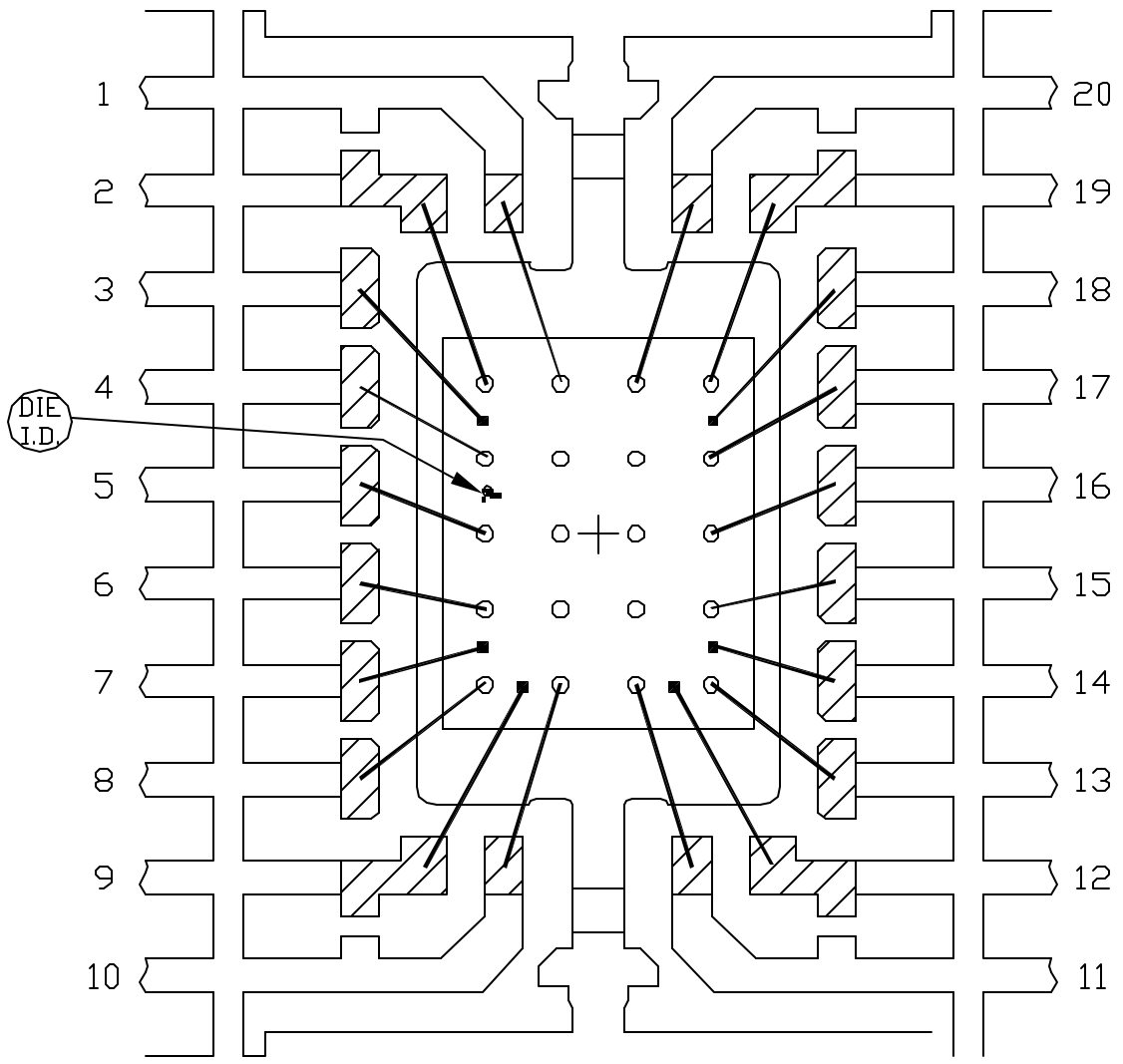
3/ Repeat pin combination I for each named Power supply and for ground

(e.g., where V_{PS1} is V_{DD} , V_{CC} , V_{SS} , V_{BB} , GND, $+V_S$, $-V_S$, V_{REF} , etc).

3.4 Pin combinations to be tested.

- a. Each pin individually connected to terminal A with respect to the device ground pin(s) connected to terminal B. All pins except the one being tested and the ground pin(s) shall be open.
- b. Each pin individually connected to terminal A with respect to each different set of a combination of all named power supply pins (e.g., V_{SS1} , or V_{SS2} or V_{SS3} or V_{CC1} , or V_{CC2}) connected to terminal B. All pins except the one being tested and the power supply pin or set of pins shall be open.
- c. Each input and each output individually connected to terminal A with respect to a combination of all the other input and output pins connected to terminal B. All pins except the input or output pin being tested and the combination of all the other input and output pins shall be open.

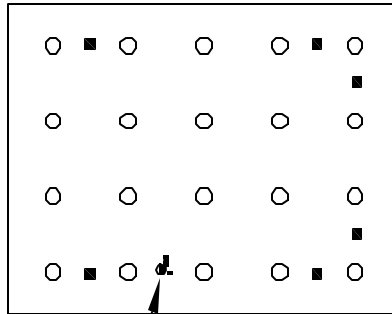




 BONDABLE AREA

PKG. CODE: U20-3		SIGNATURES	DATE	 CONFIDENTIAL & PROPRIETARY
CAV./PAD SIZE: 95x142	PKG. DESIGN			BOND DIAGRAM #: 05-9000-1673
				REV: A

ORIGINAL CHIP



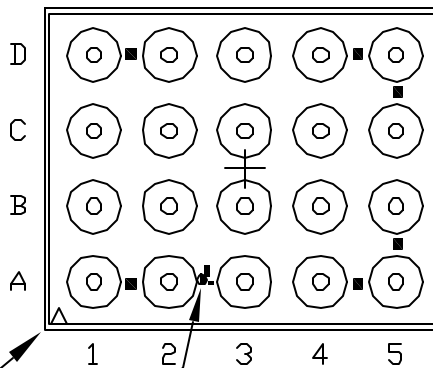
DIE I.D.

□ NORTH

□ WEST

■ EAST

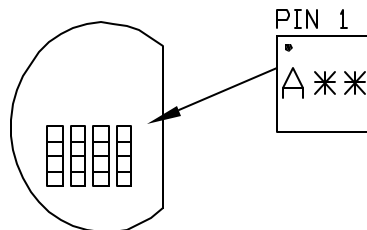
AFTER BUMP



PIN 1

□ SOUTH

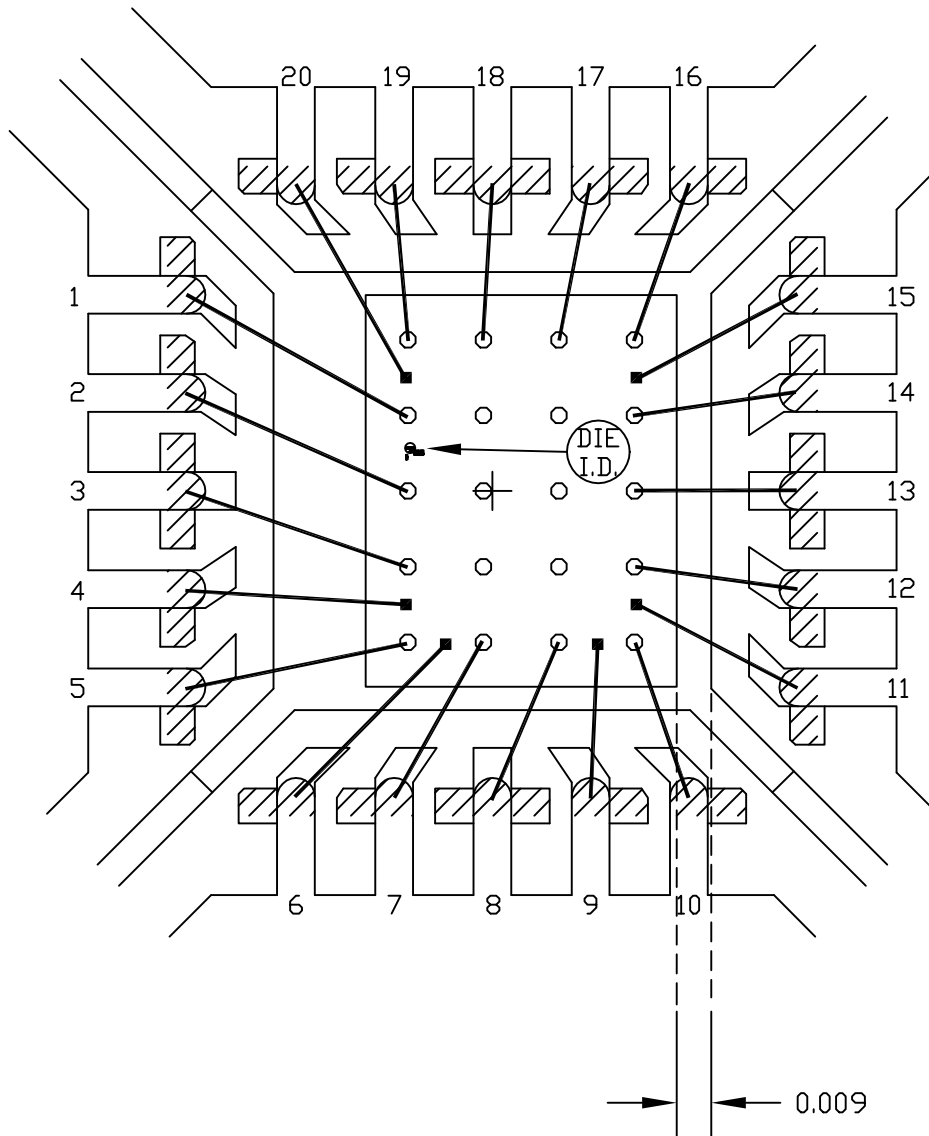
SELECT THE BOX INDICATING THE WAFER FLAT SIDE WITH RESPECT TO PIN 1.



PART MARKING ORIENTATION
IN REFERENCE TO WAFER FLAT
(MARK IS ON WAFER BACKSIDE)

PKG. CODE: B20-1		SIGNATURES	DATE	 CONFIDENTIAL & PROPRIETARY	
CAV./PAD SIZE: N/A	PKG. DESIGN			BOND DIAGRAM #: 05-9000-1672	REV: A

EXPOSED PAD PKG.



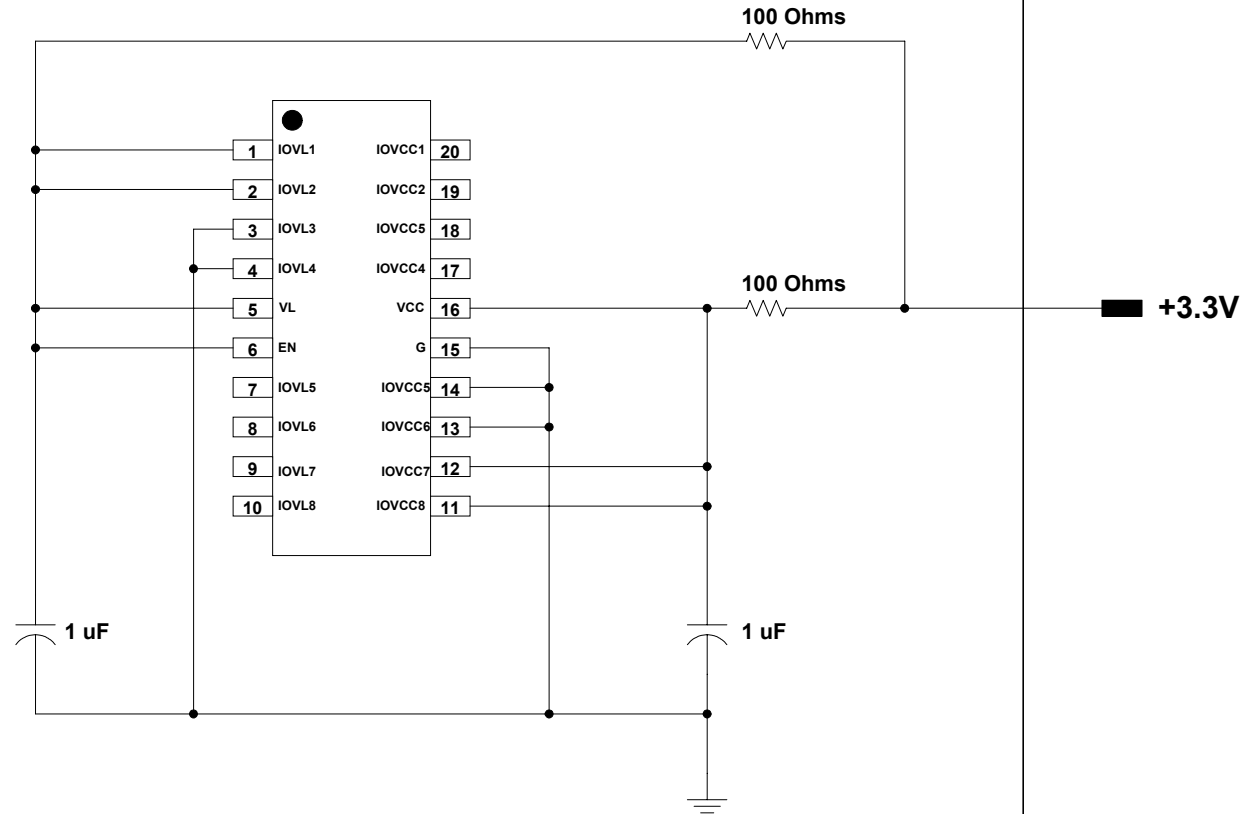
 BONDABLE AREA

PKG. BODY SIZE: 5x5 mm

PKG. CODE: G2055-1		SIGNATURES	DATE	 CONFIDENTIAL & PROPRIETARY	
CAV./PAD SIZE: 114x114	PKG. DESIGN			BOND DIAGRAM #: 05-9000-1998	REV: A

ONCE PER SOCKET

ONCE PER BOARD



DEVICES: MAX 3013 (RT64) MAX3396 (RT98)
PACKAGE: 20-TSSOP
MAX. EXPECTED CURRENT = 1mA